SOT-353 Plastic-Encapsulate Diodes

CESD5V0J4 ESD Protection Diode

DESCRIPTION

TY Semicondutor

The CESD5V0J4 is designed to protect voltage sensitive components from ESD. Excellent clamping capability, low leakage, and fast response time provide best in class protection on designs that are exposed to ESD. Because of its small size, it is suited for use in cellular phones, MP3 players, digital cameras and many other portable applications where board space is at a premium.

FEATURES

- Low Leakage
- Response Time is Typically < 1 ns
- ESD Rating of Class 3 (> 16 kV) Per Human Body Model
- IEC61000-4-2 Level 4 ESD Protection
- These are Pb-Free Devices

Maximum Ratings @Ta=25℃

Parameter	Symbol	Limit	Unit	
IEC61000-4-2(ESD)	Air	Air ±15		
	Contact		±15	KV
ESD Voltage		16	KV	
		400	V	
Peak Power Dissipation @ 8 X 20 ms @TA ≤ 2	P _{pk}	100	W	
Steady State Power 1 Diode (Note 2)	PD	200	mW	
Thermal Resistance Junction-to-Ambient	$R_{\Theta JA}$	625	°C/W	
Lead Solder Temperature - Maximum (10 Seco	ΤL	260	°C	
Junction and Storage Temperature Range	T _{j,} T _{stg}	-55 ~ +150	°C	

Stresses exceeding maximum ratings may damage the device. Maximum ratings are stress ratings only. Functional operation above the recommended. Operating conditions is not implied. Extended exposure to stresses above the recommended operating conditions may affect device reliability.

1. FR-5 = 1.0 x 0.75 x 0.62 in.

ELECTRICAL CHARACTERISTICS (Ta = 25°C unless otherwise noted, V_F = 0.9 V Max. @ I_F = 10mA for all types)

Device	Device Marking	V _{RWM} (V)	I _R (µА) @V _{RWM}		∝ (V) ⊉ I _⊺	Ι _τ	V _F (V) @I _F =200mA	V _c (V) @Max I _{PP} =5A	C (pF)
		Max	Max	Min	Max	mA	Max	Max	MAX
CESD5V0J4	12	5.0	5	6.0	7.2	1.0	1.25	12.5	35

1. Non--repetitive current per Figure 1. Derate per Figure 2.

2. Only 1 diode under power. For all 4 diodes under power, P_D will be 25%. Mounted on FR--4 board with min pad.

